

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.
 Title: ATOMIC LAYER DEPOSITED LaAlO_3 FILMS FOR GATE DIELECTRICS
 Docket No.: 1303.050US2
 Filed: February 27, 2004
 Examiner: Allan R. Wilson



Serial No.: 10/789,042
 Due Date: N/A
 Group Art Unit: 2815

MS Amendment

Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

Return postcard.
 Supplemental Information Disclosure Statement (2 pgs.), Form 1449 (4 pgs.), and copies of 7 cited documents.
 Authorization to charge Deposit Account 19-0743 in the amount of \$180.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
 Customer Number 21186

By: David R. Cochran
 Atty. David R. Cochran
 Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 25 day of May, 2006.

Lisa Rososke
 Name

Lisa Rososke
 Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
 (GENERAL)



S/N 10/789,042



MAY 30 2006

U.S. PATENT & TRADEMARK OFFICE

PATENT

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Applicant: Kie Y. Ahn et al. Examiner: Allan R. Wilson
Serial No.: 10/789,042 Group Art Unit: 2815
Filed: February 27, 2004 Docket: 1303.050US2
Title: ATOMIC LAYER-DEPOSITED LaAlO₃ FILMS FOR GATE DIELECTRICS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(c)(2), Applicants hereby authorize the Commissoner to charge the fee of \$180.00 as set forth in 37 C.F.R. § 1.17(p), to Deposit Account No. 19-0743. Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

05/31/2006 RMBRANT 00000068 190743 10789042

01 FC:1806 180.00 DA

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Minneapolis, MN 55402
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Date 25 May 2006

By David R. Cochran
David R. Cochran
Reg. No. 46,632

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Lisa Rosorslee
Name

Lisa Rosorslee
Signature

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)



Sheet No. 4

Complete if Known

Application Number	10/789,042
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2815
Examiner Name	Wilson, Allan

Attorney Docket No: 1303.050US2

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EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)

Complete if Known

Application Number	10/789,042
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Group Art Unit	2815
Examiner Name	Wilson, Allan

Sheet 2 of 4

Attorney Docket No: 1303.050US2

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<table border="1"> <tr> <td colspan="2">Complete if Known</td> </tr> <tr> <td>Application Number</td> <td>10/789,042</td> </tr> <tr> <td>Filing Date</td> <td>February 27, 2004</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2815</td> </tr> <tr> <td>Examiner Name</td> <td>Wilson, Allan</td> </tr> </table>		Complete if Known		Application Number	10/789,042	Filing Date	February 27, 2004	First Named Inventor	Ahn, Kie	Group Art Unit	2815	Examiner Name	Wilson, Allan
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T ²
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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published.	T ²
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